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View Online at https://aerobasegroup.com/nsn/5961-01-058-7789

Inclosure Material:

Metal

Overall Length:

0.421 inches

Overall Diameter:

1.281 inches

Mounting Facility Quantity:

1

Internal Configuration:

Junction contact-darlington connected

Electrode Internally-electrically Connected To Case:

Base

Mounting Method:

Threaded stud

Features Provided:

Hermetically sealed case

Thread Size:

0.164 inches

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

200.0 breakdown voltage, collector-to-base, emitter open and 200.0 breakdown voltage, collector-to-emitter, base open and 15.0 breakdown voltage, emitter-to-base, collector open

Current Rating Per Characteristic:

Between 7.50 amperes source cutoff current and 20.00 amperes source cutoff current

Power Rating Per Characteristic:

200.0 watts small-signal input power, common-collector

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius case

Special Features:

Junction pattern arrangement: npn

Test Data Document:

80131-release4201 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.).

Thread Series Designator:

Unc

Terminal Type And Quantity:

2 tab, solder lug and 1 threaded stud

Shelf Life:

N/a

Unit Of Measure:

- **Demilitarization:**

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